★ Green Device Available
★ Super Low Gate Charge
★ Excellent CdV/dt effect decline
★ Advanced high cell density Trench technology

Product Summary

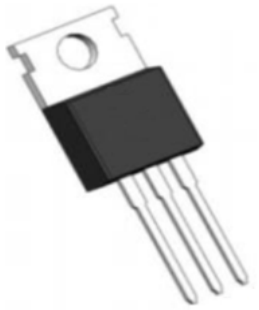
Green

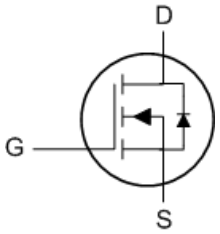
BVDSS	RDSON	ID
40V	2.4mΩ	120A

Description

The XR120N04T is the high cell density trenched N-ch MOSFETs, which provides excellent RDSON and gate charge for most of the synchronous buck converter applications. The XR120N04T meets the RoHS and Green Product requirements, 100% EAS guaranteed with full function reliability approved.

TO220AB Pin Configuration





Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1,6]	120	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1,6]	83	A
I_{DM}	Pulsed Drain Current[2]	480	A
EAS	Single Pulse Avalanche Energy[3]	441	mJ
I_{AS}	Avalanche Current	---	A
P_D@T_C=25℃	Total Power Dissipation[4]	115	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	---	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	1.3	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	40	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=1mA	---	---	---	V/ ℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=19A	---	2.4	3.0	mΩ
		V_{GS}=4.5V , I_D=19A	---	3.1	3.8	
		V_{GS}=2.5V , I_D=10A	---	---	---	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1	---	2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	---	---	mV/ ℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=40V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=40V, V_{GS}=0V , T_J=125℃	---	---	100	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=14A	---	39	---	S
Q_g	Total Gate Charge	V_{DS}=20V , V_{GS}=10V , I_D=19A	---	110	---	nC
Q_{gs}	Gate-Source Charge		---	20	---	
Q_{gd}	Gate-Drain Charge		---	20	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DS}=20V , V_{GS}=10V , R_G=6Ω , R_L=1Ω	---	14	---	ns
T_r	Rise Time		---	26	---	
$T_{d(off)}$	Turn-Off Delay Time		---	77	---	
T_f	Fall Time		---	22	---	
C_{iss}	Input Capacitance	V_{DS}=20V , V_{GS}=0V , f=1MHz	---	6130	---	pF
C_{oss}	Output Capacitance		---	401	---	
C_{rss}	Reverse Transfer Capacitance		---	348	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,4]	V_G=V_D=0V , Force Current	---	---	120	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=19A , T_J=25℃	---	---	1.2	V
t_{rr}	Reverse Recovery Time	IF=19A , di/dt=100A/μs , T_J=25℃	---	25	---	nS
Q_{rr}	Reverse Recovery Charge		---	16	---	nC

Note :

1.Repetitive Rating: Pulse width limited by maximum junction temperature.
2.E_{AS} condition: T_J=25℃,V_{DD}=40V,V_G=10V, Rg=25Ω, L=0.5mH.
3.Repetitive Rating: Pulse width limited by maximum junction temperature.

Typical Electrical And Thermal Characteristics (Curves)

Figure 1. Output Characteristics

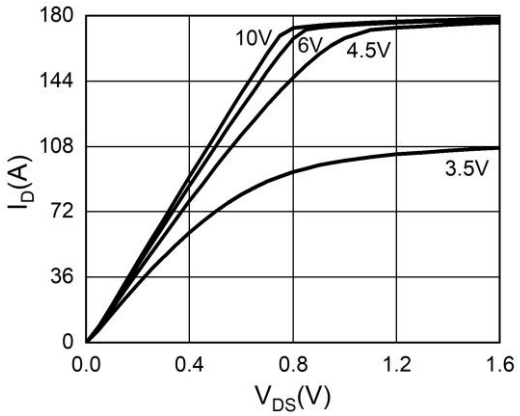


Figure 2. Transfer Characteristics

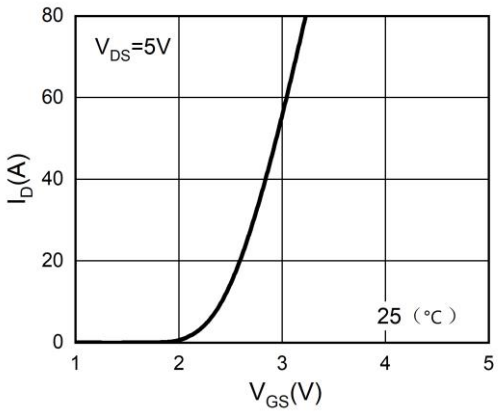


Figure 3. Power Dissipation

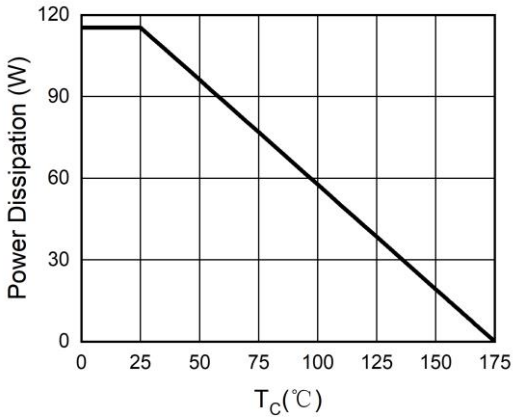


Figure 4. Drain Current

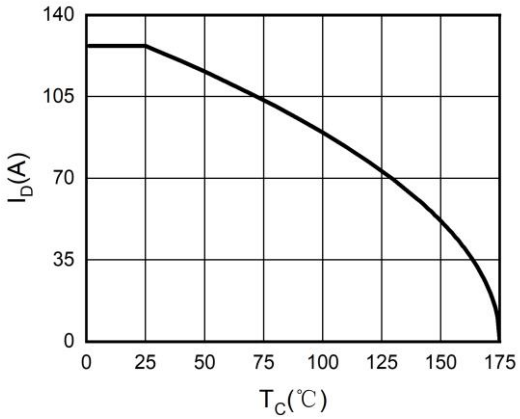


Figure 5. BV_{DSS} vs Junction Temperature

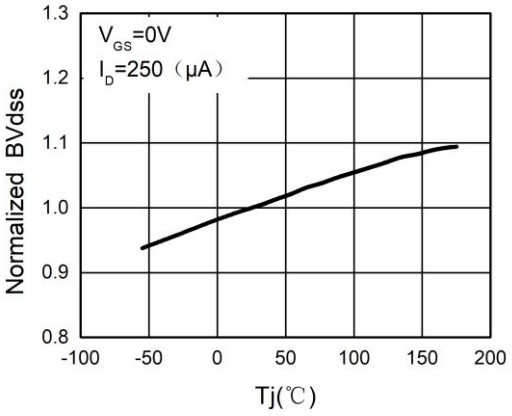
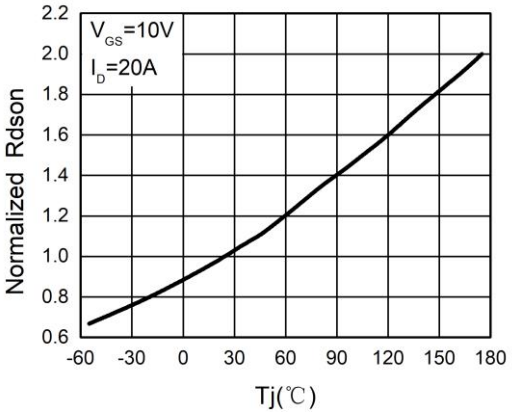


Figure 6. $R_{DS(ON)}$ vs Junction Temperature



Typical Electrical And Thermal Characteristics (Curves)

Figure 7. Gate Charge Waveforms

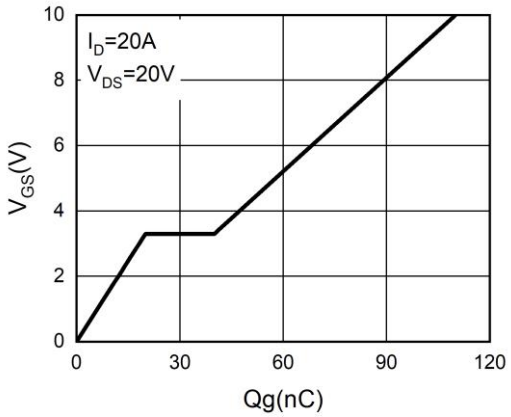


Figure 8. Capacitance

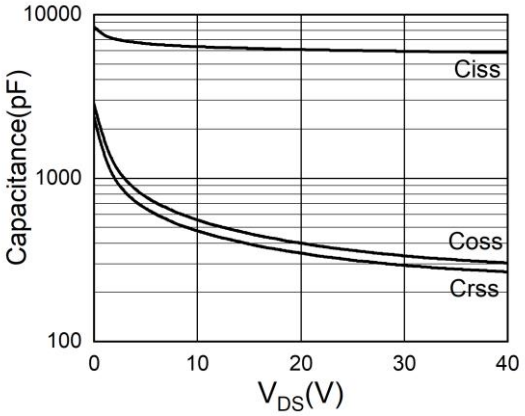


Figure 9. Body-Diode Characteristics

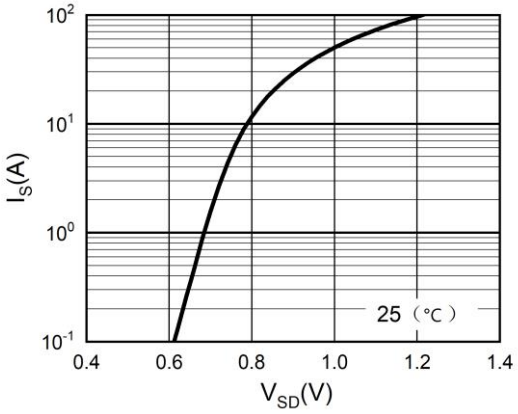
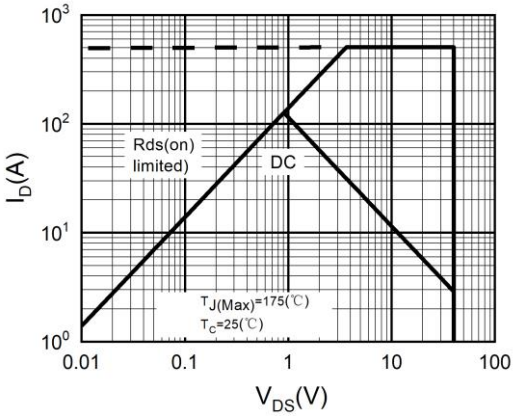


Figure 10. Maximum Safe Operating Area



Test Circuit

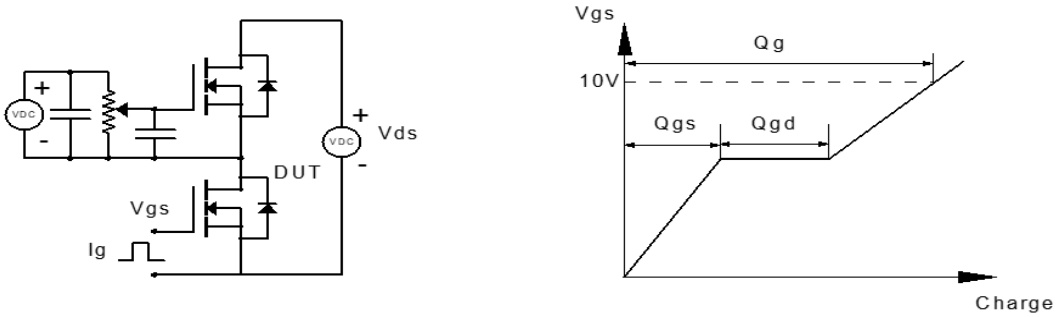


Figure 1: Gate Charge Test Circuit & Waveform

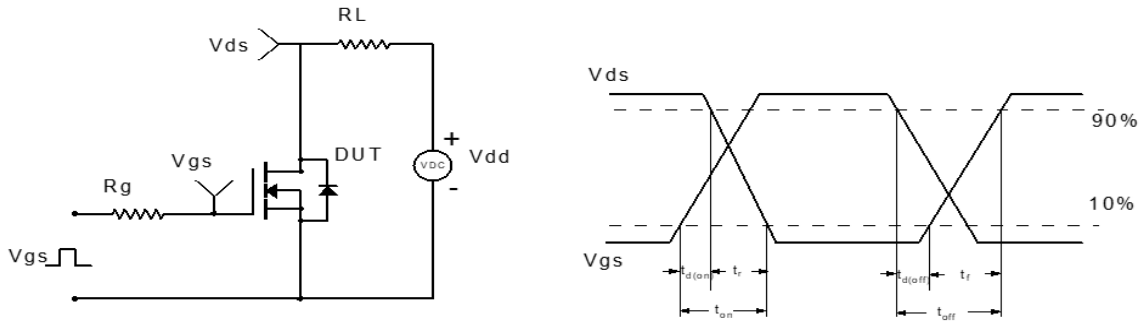


Figure 2: Resistive Switching Test Circuit & Waveform

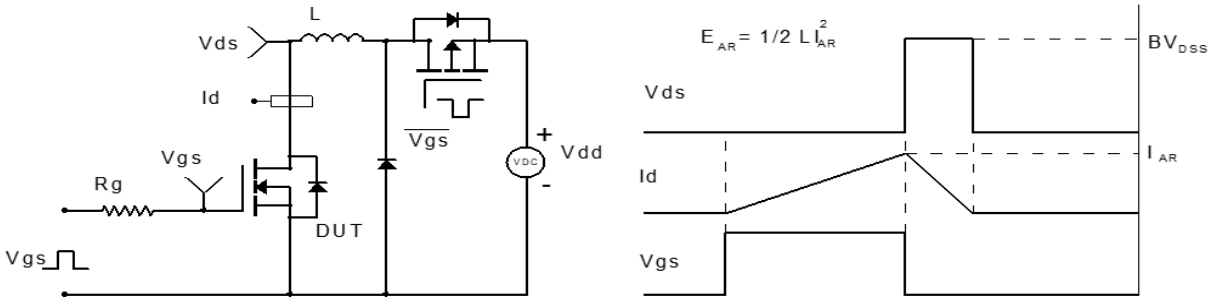


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

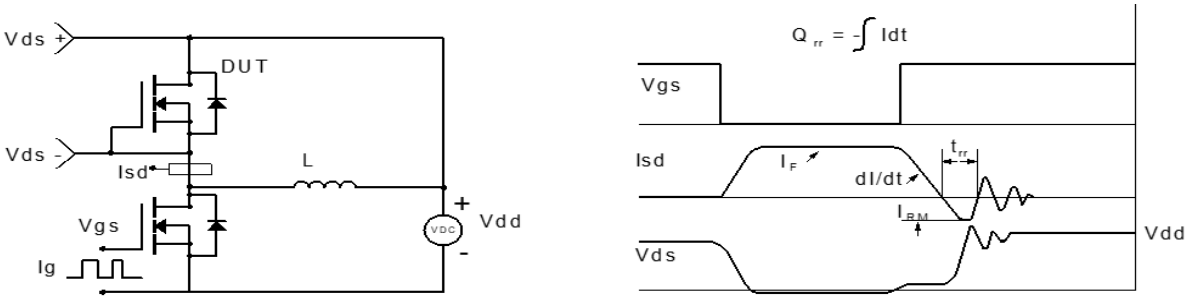
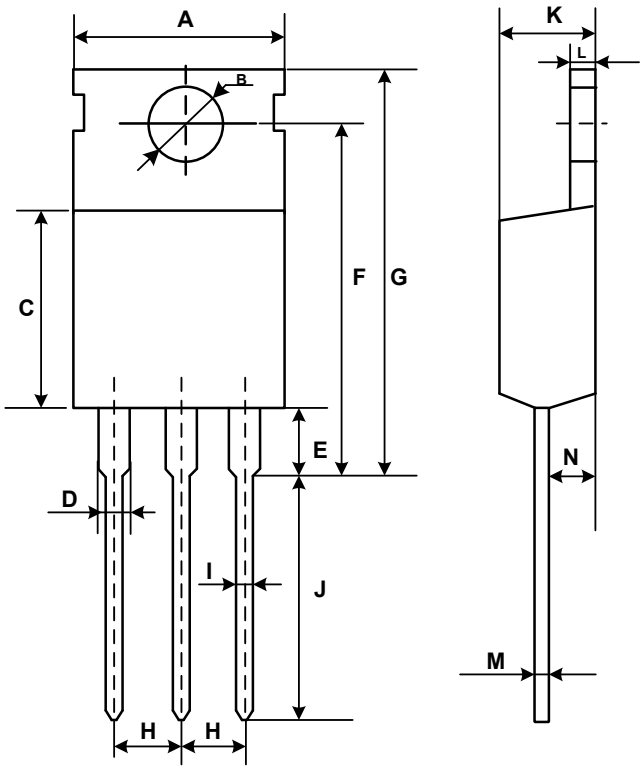


Figure 4: Diode Recovery Test Circuit & Waveform

Mechanical Dimensions for TO-220



OMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	9.70	10.30
B	3.40	3.80
C	8.80	9.40
D	1.17	1.47
E	2.60	3.50
F	15.10	16.70
G	19.55MAX	
H	2.54REF	
I	0.70	0.95
J	9.35	11.00
K	4.30	4.77
L	1.20	1.45
M	0.40	0.65
N	2.20	2.60